OPA6228UO

Ultra Orange LED Chip

Ultra Bright

AlGaInP /GaAs

1.Material

Substrate	GaAs	(N Type) Removed
Epitaxial Layer	AlGaInP	(P/N Type)

2.Electrode

N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

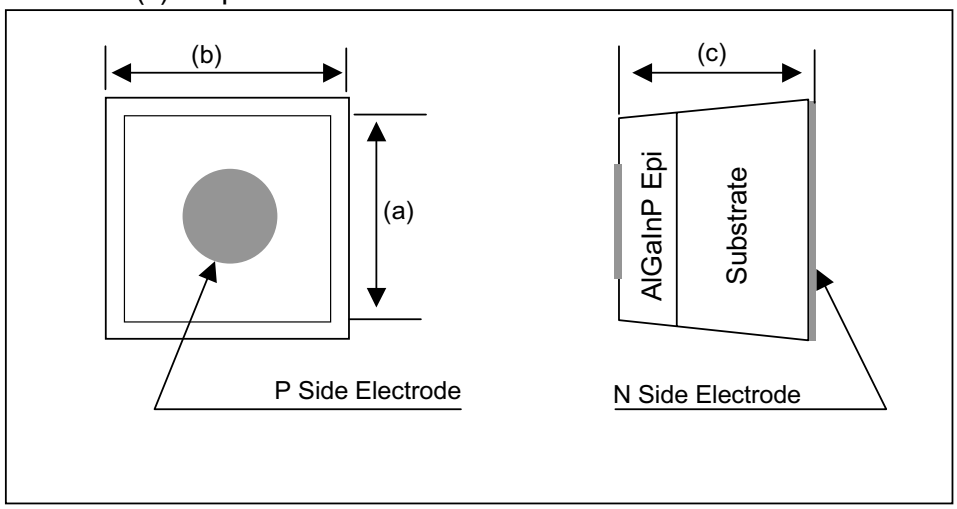
3. Electro-Optical Characteristics

Parameter	Symbol		Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$			1.7		V	I_F=1㎃
	$V_{F(2)}$			2.0	2.4	V	I_F=20㎃
Reverse Voltage	V_R		6.0			V	I_R=100㎂
Brightness	I_V	A	15	26		mcd	I_F=20㎃
		B	25	40			
		C	35	50			
		D	50	68			
		E	60	90			
		F	75	110			
Wavelength	λ_P			624		nm	I_F=20㎃
	λ_D			618		nm	I_F=20㎃
	$\Delta\lambda$			18		nm	I_F=20㎃

※ Note : Assembled into TO-18 Header without resin coating.

4. Mechanical Data

(a) Emission Area ---------- 10mil × 10mil
(b) Bottom Area ---------- 11mil × 11mil
(c) Chip Thickness ---------- 7mil



Knowledge*on Inc.
For more information, visit our website at www.knowledge-on.com
513-37 Eoyang-dong, Iksan, 570-210, Korea. Tel: +82-63-839-1111. Fax: +82-63-835-8259

Certificate No. Q9757

Downloaded from Elcodis.com electronic components distributor